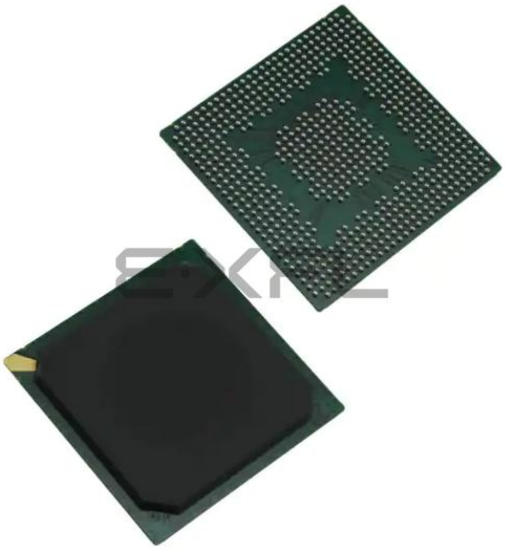

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (3)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8343eczqaddb

Email: info@E-XFL.COM Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

— Address translation units for address mapping between host and peripheral
— Dual address cycle for target
— Internal configuration registers accessible from PCI
- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, IEEE Std. 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs):
— Public key execution unit (PKEU) :
  – RSA and Diffie-Hellman algorithms
  – Programmable field size up to 2048 bits
  – Elliptic curve cryptography
  – F2m and F(p) modes
  – Programmable field size up to 511 bits
— Data encryption standard (DES) execution unit (DEU)
  – DES and 3DES algorithms
  – Two key (K1, K2) or three key (K1, K2, K3) for 3DES
  – ECB and CBC modes for both DES and 3DES
— Advanced encryption standard unit (AESU)
  – Implements the Rijndael symmetric-key cipher
  – Key lengths of 128, 192, and 256 bits
  – ECB, CBC, CCM, and counter (CTR) modes
— XOR parity generation accelerator for RAID applications
— ARC four execution unit (AFEU)
  – Stream cipher compatible with the RC4 algorithm
  – 40- to 128-bit programmable key
— Message digest execution unit (MDEU)
  – SHA with 160-, 224-, or 256-bit message digest
  – MD5 with 128-bit message digest
  – HMAC with either algorithm
— Random number generator (RNG)
— Four crypto-channels, each supporting multi-command descriptor chains
  – Static and/or dynamic assignment of crypto-execution units through an integrated controller
  – Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
- Universal serial bus (USB) dual role controller
— USB on-the-go mode with both device and host functionality
— Complies with USB specification Rev. 2.0
— Can operate as a stand-alone USB device
  – One upstream facing port
  – Six programmable USB endpoints

supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current from 3A to 5A. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{PORESET}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

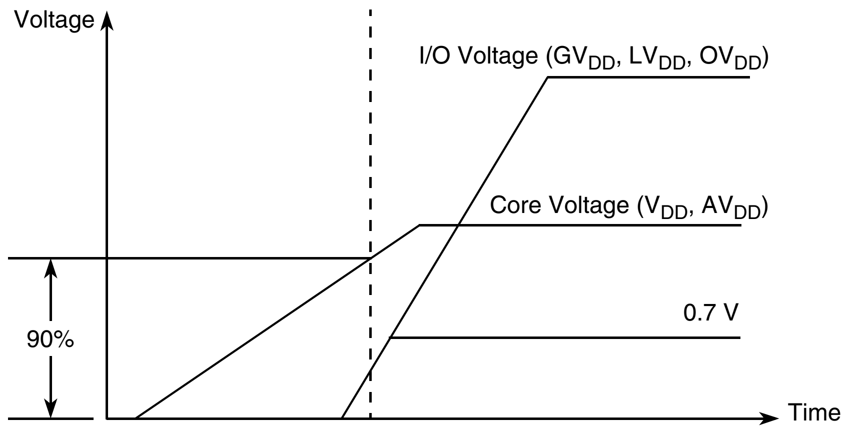


Figure 4. Power Sequencing Example

I/O voltage supplies (GV_{DD}, LV_{DD}, and OV_{DD}) do not have any ordering requirements with respect to one another.

3 Power Characteristics

The estimated typical power dissipation for the MPC8343EA device is shown in Table 4.

Table 4. MPC8343EA Power Dissipation[1]

	Core Frequency (MHz)	CSB Frequency (MHz)	Typical at T_J = 65	Typical[2,3]	Maximum[4]	Unit
PBGA	266	266	1.3	1.6	1.8	W
		133	1.1	1.4	1.6	W
	400	266	1.5	1.9	2.1	W
		133	1.4	1.7	1.9	W
	400	200	1.5	1.8	2.0	W
		100	1.3	1.7	1.9	W

1 The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 5.
2 Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
3 Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.
4 Maximum power is based on a voltage of V_{DD} = 1.2 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.

5.2 RESET AC Electrical Characteristics

Table 10 provides the reset initialization AC timing specifications of the MPC8343EA.

Table 10. RESET Initialization Timing Specifications

Parameter	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$ or $\overline{\text{SRESET}}$ (input) to activate reset flow	32	—	$t_{PCI\_SYNC\_IN}$	1
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to CLKIN when the MPC8343EA is in PCI host mode	32	—	t_{CLKIN}	2
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to PCI_SYNC_IN when the MPC8343EA is in PCI agent mode	32	—	$t_{PCI\_SYNC\_IN}$	1
$\overline{\text{HRESET}}$/$\overline{\text{SRESET}}$ assertion (output)	512	—	$t_{PCI\_SYNC\_IN}$	1
$\overline{\text{HRESET}}$ negation to $\overline{\text{SRESET}}$ negation (output)	16	—	$t_{PCI\_SYNC\_IN}$	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the MPC8343EA is in PCI host mode	4	—	t_{CLKIN}	2
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the MPC8343EA is in PCI agent mode	4	—	$t_{PCI\_SYNC\_IN}$	1
Input hold time for POR configuration signals with respect to negation of $\overline{\text{HRESET}}$	0	—	ns	—
Time for the MPC8343EA to turn off POR configuration signals with respect to the assertion of $\overline{\text{HRESET}}$	—	4	ns	3
Time for the MPC8343EA to turn on POR configuration signals with respect to the negation of $\overline{\text{HRESET}}$	1	—	$t_{PCI\_SYNC\_IN}$	1, 3

Notes:
1. $t_{PCI\_SYNC\_IN}$ is the clock period of the input clock applied to PCI_SYNC_IN. In PCI host mode, the primary clock is applied to the CLKIN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual*.
2. t_{CLKIN} is the clock period of the input clock applied to CLKIN. It is valid only in PCI host mode. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual*.
3. POR configuration signals consist of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

Table 11 lists the PLL and DLL lock times.

Table 11. PLL and DLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	µs	—
DLL lock times	7680	122,880	csb_clk cycles	1, 2

Notes:
1. DLL lock times are a function of the ratio between the output clock and the coherency system bus clock (csb_clk). A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.
2. The csb_clk is determined by the CLKIN and system PLL ratio. See Section 19, “Clocking.”

Table 13 provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR SDRAM component(s) when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.18	V	—
Output leakage current	I_{OZ}	–9.9	–9.9	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 15 provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
266 MHz		–750	750		—
200 MHz		–750	750		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the equation: $t_{DISKEW} = \pm (T/4 - \text{abs}(t_{CISKEW}))$; where T is the clock period and abs (t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. This specification applies only to the DDR interface.

Figure 5 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

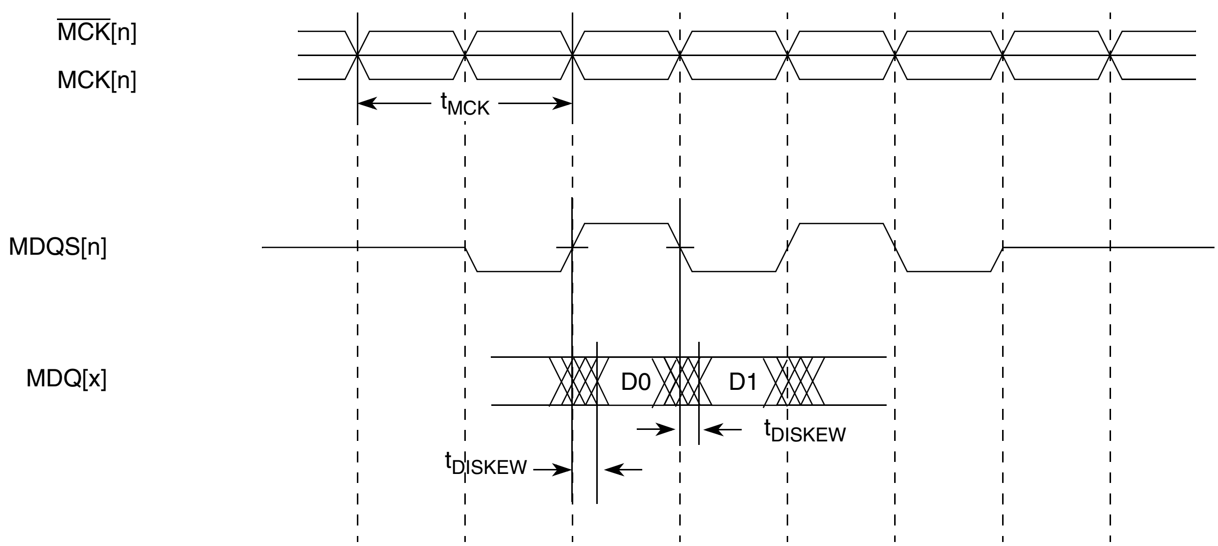


Figure 5. DDR Input Timing Diagram

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 shows the DDR and DDR2 output AC timing specifications.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/$\overline{\text{MCK}}$[n] crossing)	t_{MCK}	7.5	10	ns	2
ADDR/CMD/MODT output setup with respect to MCK	t_{DDKHAS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		

Figure 7 shows the DDR SDRAM output timing diagram.

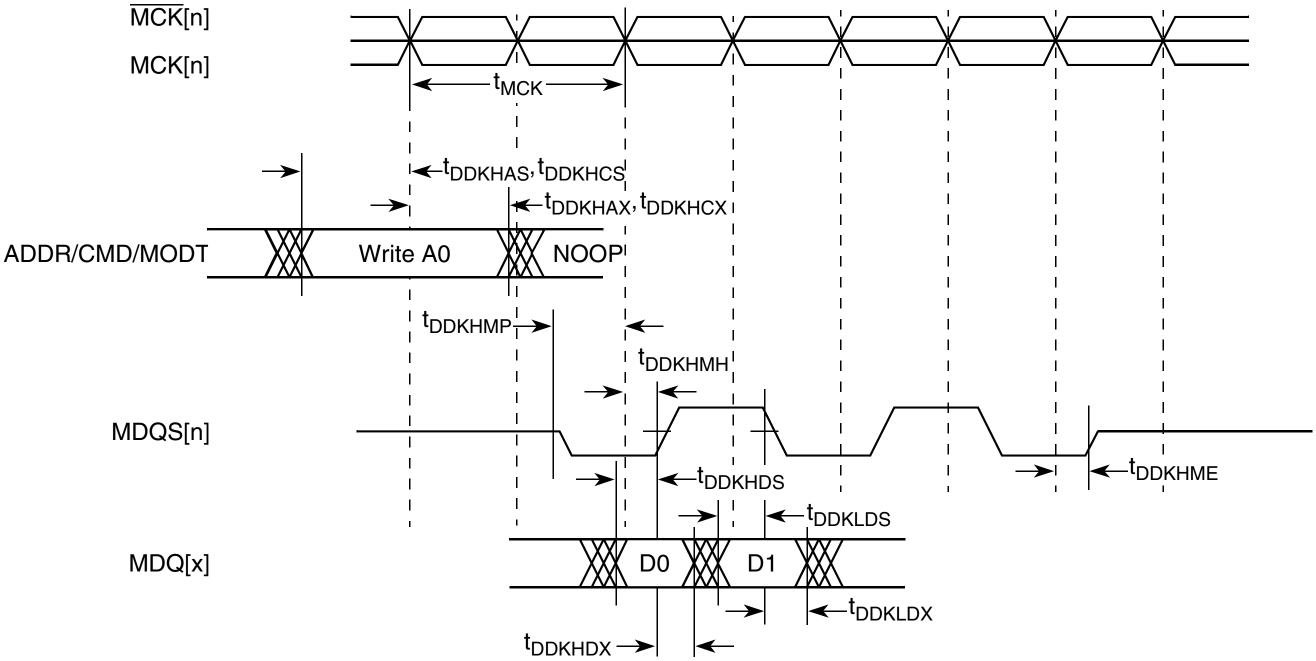


Figure 7. DDR SDRAM Output Timing Diagram

Figure 8 provides the AC test load for the DDR bus.

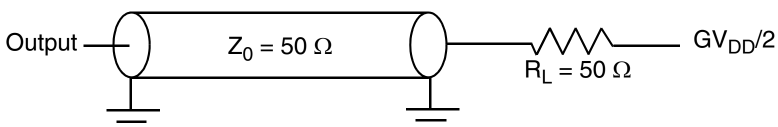


Figure 8. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8343EA.

7.1 DUART DC Electrical Characteristics

Table 21 provides the DC electrical characteristics for the DUART interface of the MPC8343EA.

Table 21. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (0.8 V ≤ V_{IN} ≤ 2 V)	I_{IN}	—	±5	μA

8.1.1 TSEC DC Electrical Characteristics

MII, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 23 and Table 24. The RGMII and RTBI signals in Table 24 are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 23. MII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD}[2]	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	LV_{DD} = Min	2.40	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	40	μA
Input low current	I_{IL}	V_{IN}[1] = GND		–600	—	μA

Notes:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.
2. MII pins not needed for RGMII or RTBI operation are powered by the OV_{DD} supply.

Table 24. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	10	μA
Input low current	I_{IL}	V_{IN}[1] = GND		–15	—	μA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2.1.2 MII Receive AC Timing Specifications

Table 26 provides the MII receive AC timing specifications.

Table 26. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise (20%–80%)	t_{MRXR}	1.0	—	4.0	ns
RX_CLK clock fall time (80%–20%)	t_{MRXF}	1.0	—	4.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 10 provides the AC test load for TSEC.

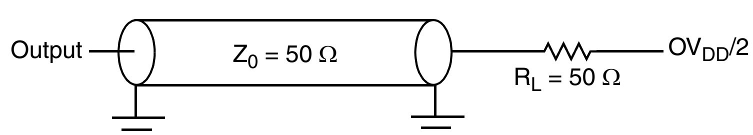


Figure 10. TSEC AC Test Load

Figure 11 shows the MII receive AC timing diagram.

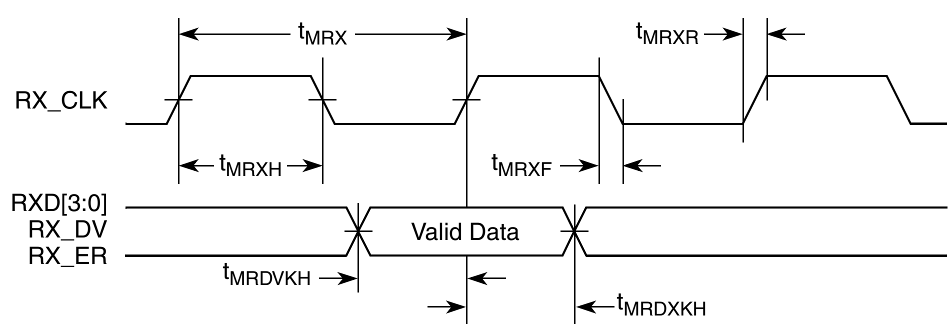


Figure 11. MII Receive AC Timing Diagram

8.2.2 RGMII and RTBI AC Timing Specifications

Table 27 presents the RGMII and RTBI AC timing specifications.

Table 27. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}	–0.5	—	0.5	ns
Data to clock input skew (at receiver)[2]	t_{SKRGT}	1.0	—	2.8	ns
Clock cycle duration[3]	t_{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T[4, 5]	t_{RGTH}/t_{RGT}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX[3, 5]	t_{RGTH}/t_{RGT}	40	50	60	%
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns
Fall time (80%–20%)	t_{RGTF}	—	—	0.75	ns

Notes:

1. In general, the clock reference symbol for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Also, the notation for rise (R) and fall (F) times follows the clock symbol. For symbols representing skews, the subscript is SK followed by the clock being skewed (RGT).
2. This implies that PC board design requires clocks to be routed so that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned.
5. Duty cycle reference is $LV_{DD}/2$.

Figure 12 shows the RBMII and RTBI AC timing and multiplexing diagrams.

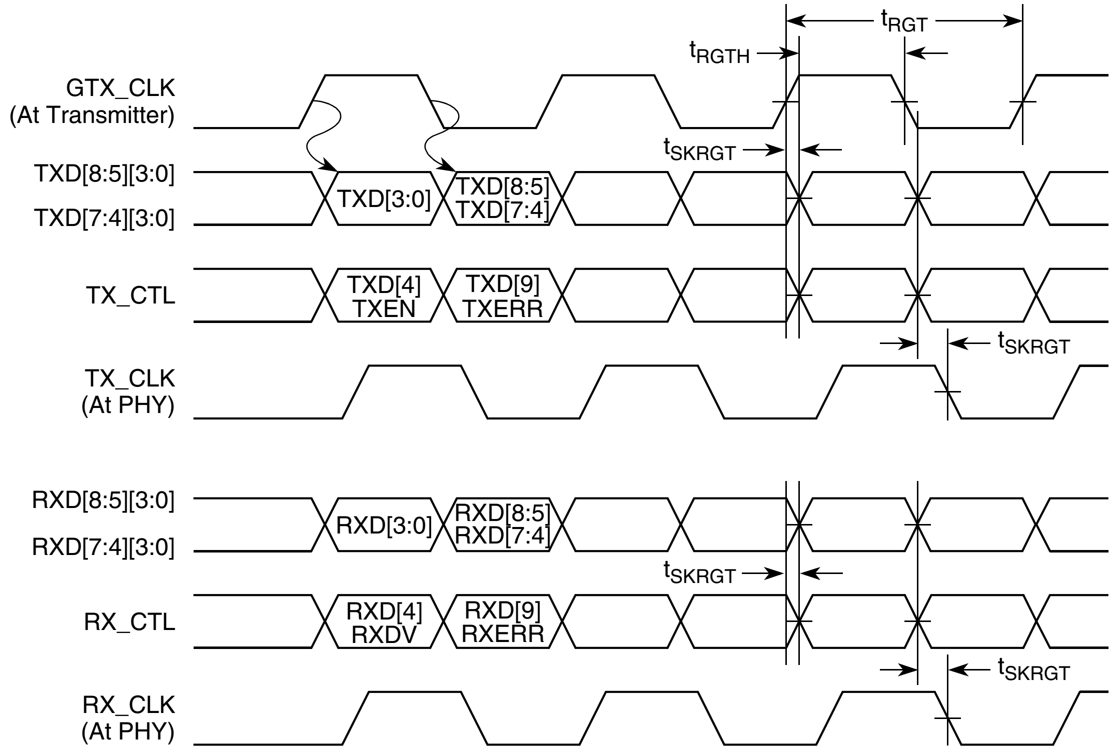


Figure 12. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to the MII management interface signals management data input/output (MDIO) and management data clock (MDC). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (TSEC)—MII/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 2.5 or 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 28 and Table 29.

Table 28. MII Management DC Electrical Characteristics Powered at 2.5 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (2.5 V)	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	—	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V

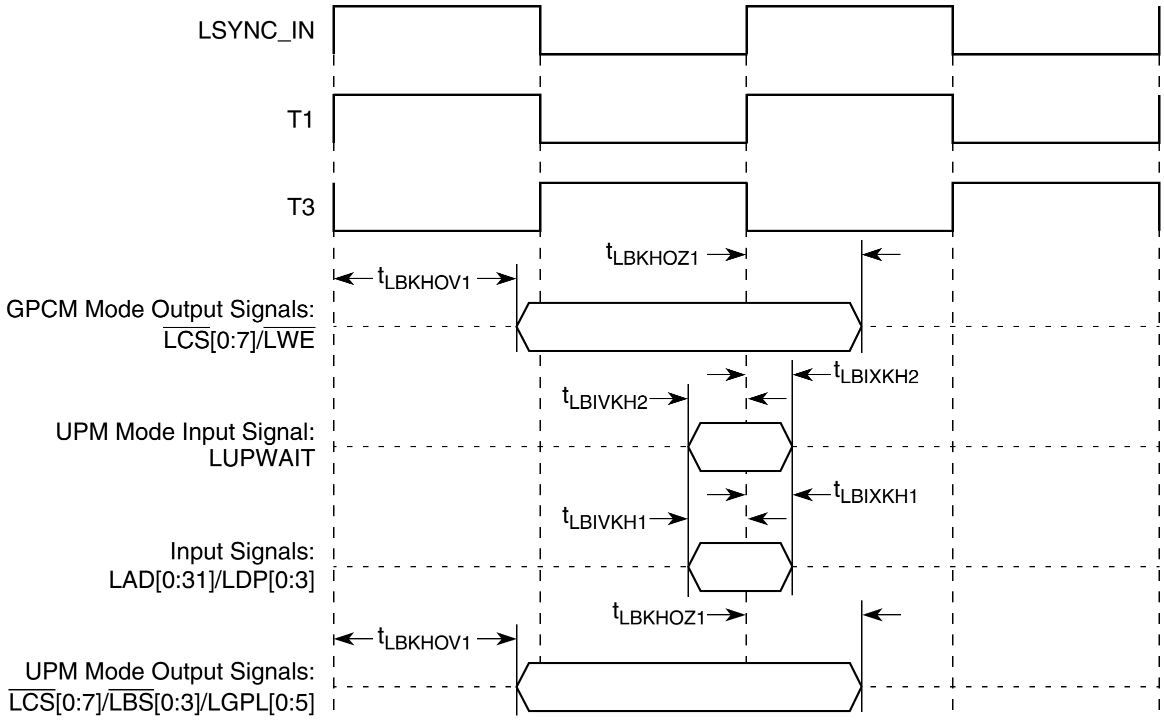


Figure 19. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

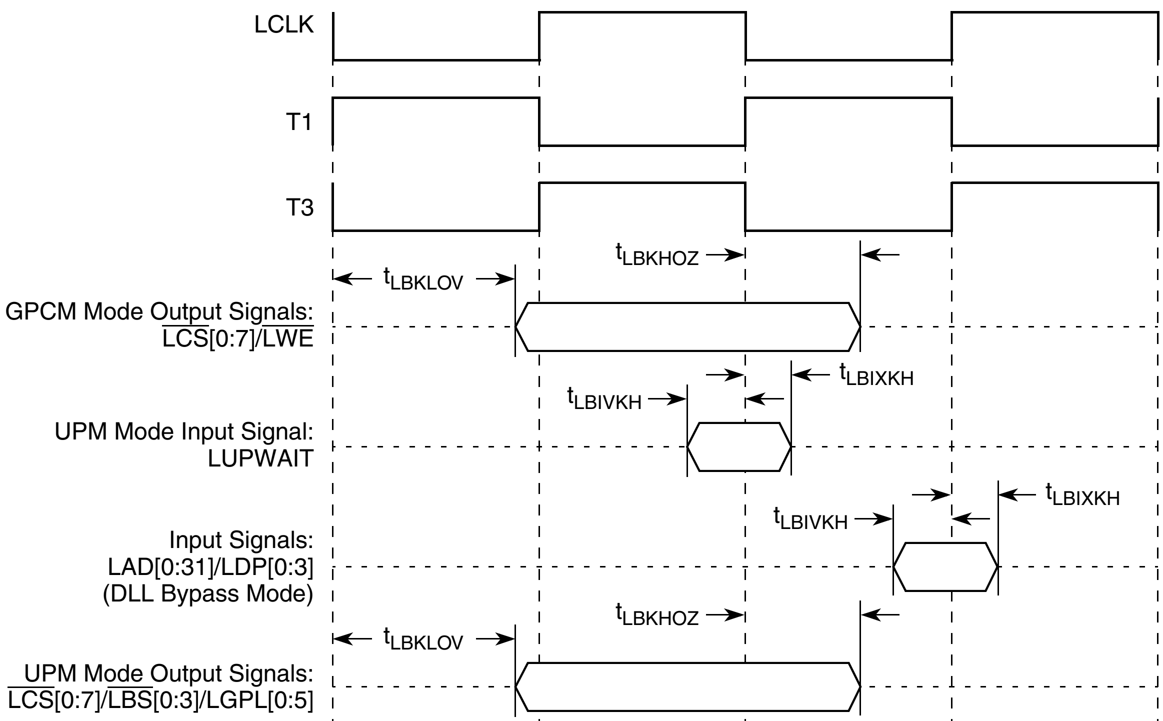


Figure 20. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)

Table 36. JTAG Interface DC Electrical Characteristics (continued)

Parameter	Symbol	Condition	Min	Max	Unit
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

11.2 JTAG AC Timing Specifications

This section describes the AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8343EA. Table 37 provides the JTAG AC timing specifications as defined in Figure 24 through Figure 27.

Table 37. JTAG AC Timing Specifications (Independent of CLKIN)[1]

At recommended operating conditions (see Table 2).

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t_{JTGR}, t_{JTGF}	0	2	ns	—
$\overline{TRST}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t_{JTDVKH} t_{JTIVKH}	4 4	— —	ns	4
Input hold times: Boundary-scan data TMS, TDI	t_{JTDXKH} t_{JTIXKH}	10 10	— —	ns	4
Valid times: Boundary-scan data TDO	t_{JTKLDV} t_{JTKLOV}	2 2	11 11	ns	5
Output hold times: Boundary-scan data TDO	t_{JTKLDX} t_{JTKLOX}	2 2	— —	ns	5

Table 41. PCI AC Timing Specifications at 66 MHz[1] (continued)

Parameter	Symbol[2]	Min	Max	Unit	Notes
Input hold from clock	t_{PCIXKH}	0	—	ns	3, 5

Notes:
1. PCI timing depends on M66EN and the ratio between PCI1/PCI2. Refer to the PCI chapter of the reference manual for a description of M66EN.
2. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
3. See the timing measurement conditions in the *PCI 2.3 Local Bus Specifications*.
4. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Input timings are measured at the pin.

Table 42 provides the PCI AC timing specifications at 33 MHz.

Table 42. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	11	ns	2
Output hold from clock	t_{PCKHOX}	2	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0	—	ns	2, 4

Notes:
1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.3 Local Bus Specifications*.
3. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.

Figure 30 provides the AC test load for PCI.

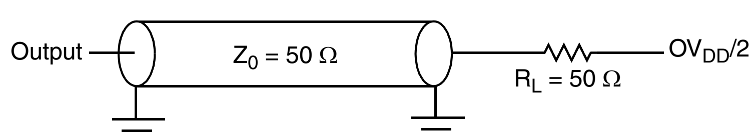


Figure 30. PCI AC Test Load

Figure 31 shows the PCI input AC timing diagram.

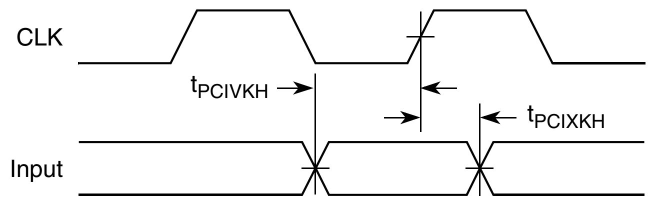


Figure 31. PCI Input AC Timing Diagram

Figure 32 shows the PCI output AC timing diagram.

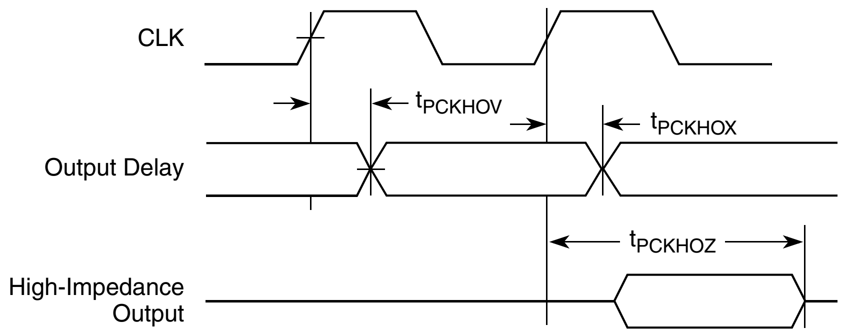


Figure 32. PCI Output AC Timing Diagram

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

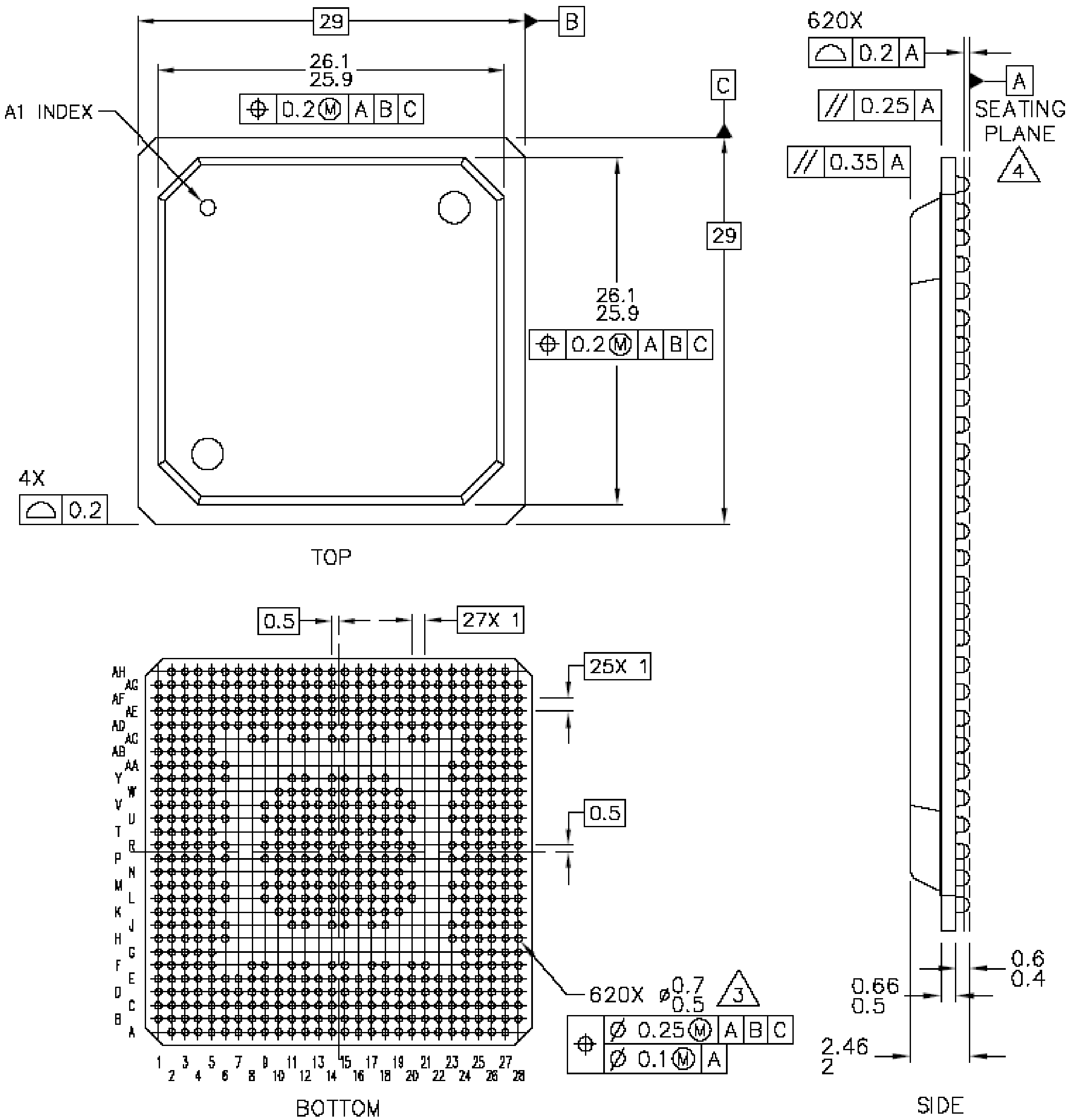
Table 43 provides the DC electrical characteristics for the MPC8343EA timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Table 43. Timer DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

18.2 Mechanical Dimensions for the MPC8343EA PBGA

Figure 36 shows the mechanical dimensions and bottom surface nomenclature for the MPC8343EA, 620-PBGA package.



Notes:

1. All dimensions are in millimeters.
2. Dimensioning and tolerancing per ASME Y14. 5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Figure 36. Mechanical Dimensions and Bottom Surface Nomenclature for the MPC8343EA PBGA

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SPI				
SPIMOSI/$\overline{\text{LCS}}$[6]	D7	I/O	OV_{DD}	—
SPIMISO/$\overline{\text{LCS}}$[7]	C7	I/O	OV_{DD}	—
SPICLK	B7	I/O	OV_{DD}	—
SPISEL	A7	I	OV_{DD}	—
Clocks				
PCI_CLK_OUT[0:2]	Y1, W3, W2	O	OV_{DD}	—
PCI_CLK_OUT[3]/$\overline{\text{LCS}}$[6]	W1	O	OV_{DD}	—
PCI_CLK_OUT[4]/$\overline{\text{LCS}}$[7]	V3	O	OV_{DD}	—
PCI_SYNC_IN/PCI_CLOCK	U4	I	OV_{DD}	—
PCI_SYNC_OUT	U5	O	OV_{DD}	3
RTC/PIT_CLOCK	E9	I	OV_{DD}	—
CLKIN	W5	I	OV_{DD}	—
JTAG				
TCK	H27	I	OV_{DD}	—
TDI	H28	I	OV_{DD}	4
TDO	M24	O	OV_{DD}	3
TMS	J27	I	OV_{DD}	4
$\overline{\text{TRST}}$	K26	I	OV_{DD}	4
Test				
TEST	F28	I	OV_{DD}	6
TEST_SEL	T3	I	OV_{DD}	7
PMC				
$\overline{\text{QUIESCE}}$	K27	O	OV_{DD}	—
System Control				
$\overline{\text{PORESET}}$	K28	I	OV_{DD}	—
$\overline{\text{HRESET}}$	M25	I/O	OV_{DD}	1
$\overline{\text{SRESET}}$	L27	I/O	OV_{DD}	2
Thermal Management				
THERM0	B15	I	—	8

19 Clocking

Figure 37 shows the internal distribution of the clocks.

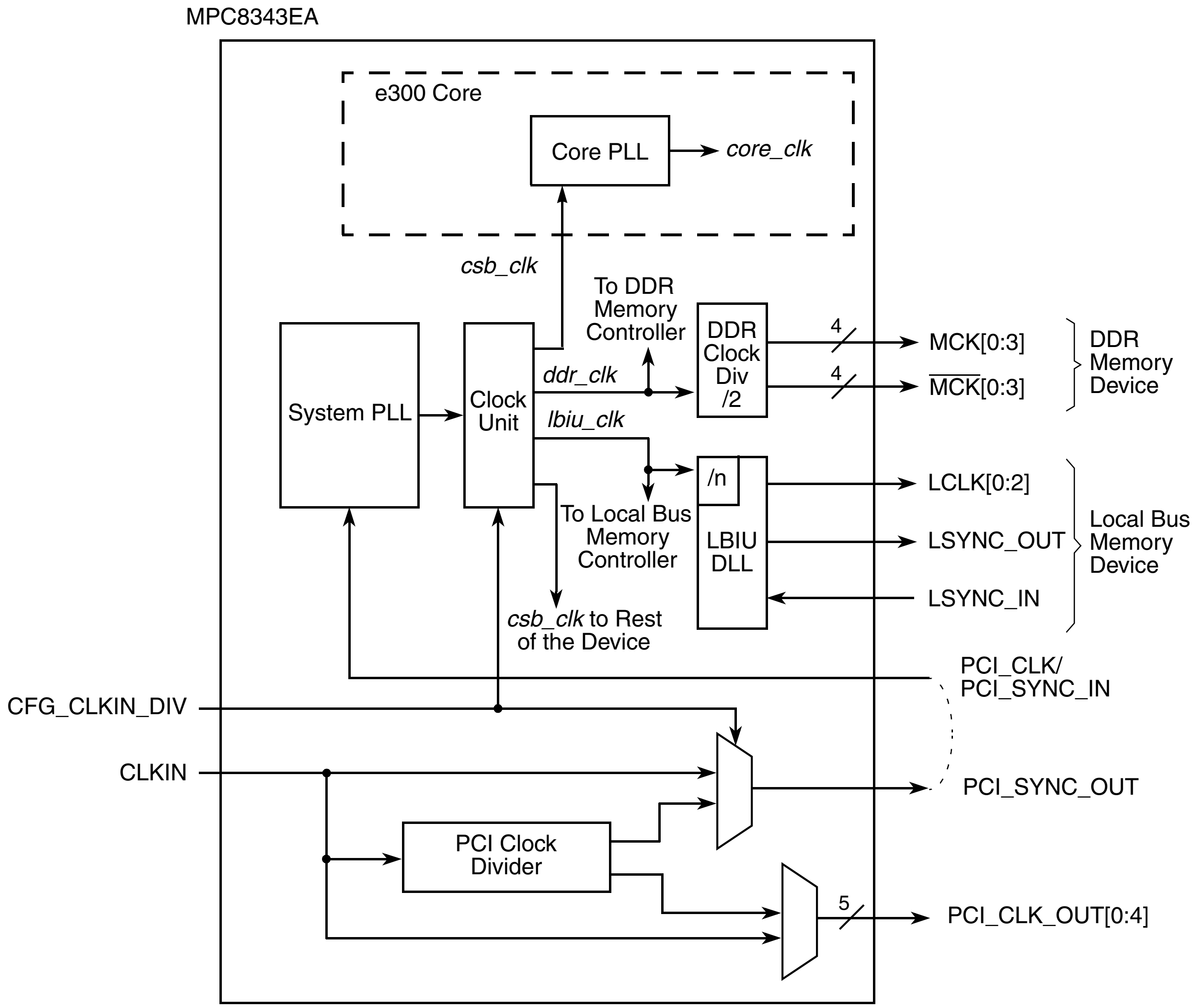


Figure 37. MPC8343EA Clock Subsystem

The primary clock source can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. When the MPC8343EA is configured as a PCI host device, CLKIN is its primary input clock. CLKIN feeds the PCI clock divider (÷2) and the multiplexors for PCI_SYNC_OUT and PCI_CLK_OUT. The CFG_CLKIN_DIV configuration input selects whether CLKIN or CLKIN/2 is driven out on the PCI_SYNC_OUT signal. The OCCR[PCICD*n*] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUT*n* signals.

PCI_SYNC_OUT is connected externally to PCI_SYNC_IN to allow the internal clock subsystem to synchronize to the system PCI clocks. PCI_SYNC_OUT must be connected properly to PCI_SYNC_IN, with equal delay to all PCI agent devices in the system, to allow the MPC8343EA to function. When the device is configured as a PCI agent device, PCI_CLK is the primary input clock and the CLKIN signal should be tied to GND.

Table 53 provides the operating frequencies for the MPC8343EA PBGA under recommended operating conditions.

Table 53. Operating Frequencies for PBGA

Parameter[1]	266 MHz	333 MHz	400 MHz	Unit
e300 core frequency (*core_clk*)	200–266	200–333	200–400	MHz
Coherent system bus frequency (*csb_clk*)		100–266		MHz
DDR1 memory bus frequency (MCK)[2]		100–133		MHz
DDR2 memory bus frequency (MCK)[3]		100–133		MHz
Local bus frequency (LCLK*n*)[4]		16.67–133		MHz
PCI input frequency (CLKIN or PCI_CLK)		25–66		MHz
Security core maximum internal operating frequency		133		MHz
USB_DR, USB_MPH maximum internal operating frequency		133		MHz

1 The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM], and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the Security core and USB modules does not exceed the respective values listed in this table.

2 The DDR data rate is 2× the DDR memory bus frequency.

3 The DDR data rate is 2× the DDR memory bus frequency.

4 The local bus frequency is ½, ¼, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWL[LBIUCM]).

19.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 54 shows the multiplication factor encodings for the system PLL.

Table 54. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10

Table 54. System PLL Multiplication Factors (continued)

RCWL[SPMF]	System PLL Multiplication Factor
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

As described in Section 19, “Clocking,” the LBIUCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 55 and Table 56 show the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 55. CSB Frequency Options for Host Mode

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0010	2 : 1				133
Low	0011	3 : 1			100	200
Low	0100	4 : 1		100	133	266
Low	0101	5 : 1		125	166	333
Low	0110	6 : 1	100	150	200	
Low	0111	7 : 1	116	175	233	
Low	1000	8 : 1	133	200	266	
Low	1001	9 : 1	150	225	300	
Low	1010	10 : 1	166	250	333	
Low	1011	11 : 1	183	275		
Low	1100	12 : 1	200	300		
Low	1101	13 : 1	216	325		
Low	1110	14 : 1	233			
Low	1111	15 : 1	250			
Low	0000	16 : 1	266			

that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

20.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

Some application environments require a heat sink to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

$R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

The thermal performance of devices with heat sinks has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

Table 60 shows heat sink thermal resistance for PBGA of the MPC8343EA.

Table 60. Heat Sink and Thermal Resistance of MPC8343EA (PBGA)

Heat Sink Assuming Thermal Grease	Air Flow	29 × 29 mm PBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	13.5
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	9.6
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	8.8
AAVID 31 × 35 × 23 mm pin fin	Natural convection	11.3
AAVID 31 × 35 × 23 mm pin fin	1 m/s	8.1
AAVID 31 × 35 × 23 mm pin fin	2 m/s	7.5
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	9.1
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	7.1
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	6.5
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	10.1